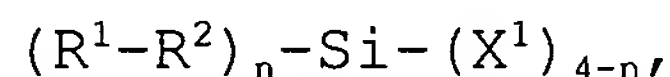


IN THE CLAIMS:

1. (original) A method for forming a low dielectric constant structure on a semiconductor substrate by CVD processing, comprising the steps of:

- introducing a material gas into a reaction chamber for CVD processing, wherein a semiconductor substrate is placed, said material gas comprising a silicon-containing chemical compound having the formula of



wherein

X^1 is hydrogen, halogen, acyloxy, alkoxy or OH group,

R^2 is an optional group and comprises an aromatic group having 5 to 7 carbon atoms, and

R^1 is a substituent at position 4 of R^2 or a group directly linked to Si, selected from hydrocarbyl groups having from 1 to 30 carbons;

n is an integer 1-3; and

- forming a silicone polymer film on the semiconductor substrate by activating a polymerization reaction in the reaction chamber where the material gas is present until

the relative dielectric constant of the silicone polymer film is lower than a predetermined value.

2 - 16. (canceled)

17. (original) A poly(organo siloxane) compound formed via CVD process comprising a repeating Si-O backbone, carbon chain crosslinking groups and $-R^1-R^2$ bound to from 5 % to 60 % of the silicon atoms in the Si-O backbone, wherein R^2 is an aromatic group having 6 carbon atoms and R^1 is a substituent at position 4 of R^2 .

18 - 34. (canceled)

35. (original) A poly(organo siloxane) compound formed via the CVD method comprising a repeating Si-O backbone, $-R^1-R^2$ bound to from 25 % to 60 % of the silicon atoms in the Si-O backbone, wherein R^2 is an aromatic group having 6 carbon atoms and R^1 is a substituent at position 4 of R^2 or a group directly linked to Si, and R^3 is bound to from 5 % to 60 % of the silicon atoms, wherein R^3 is an alkenyl group having from 2 to 5 carbon atoms, acrylic group or epoxy group.

36 - 50. (canceled)

51. (original) An integrated circuit having a layer with areas of an electrically conductive first material and an electrically insulating second material, wherein the second material is a poly(organo siloxane) compound deposited via CVD method comprising a repeating Si-O backbone, carbon chain crosslinking groups and -R¹-R² bound to from 5 % to 60 % of the silicon atoms in the Si-O backbone, wherein R² is an aromatic group having 6 carbon atoms and R¹ is a substituent at position 4 of R².

52 - 61. (canceled)

62. (original) A computer comprising an integrated circuit having a layer with areas of an electrically conductive first material and an electrically insulating second material, wherein the second material is a poly(organo siloxane) compound deposited via CVD method comprising a repeating Si-O backbone, carbon chain crosslinking groups and -R¹-R² bound to from 5 % to 60 % of the silicon atoms in the Si-O backbone, wherein R² is an aromatic group having 6 carbon atoms and R¹ is a substituent at position 4 of R².

63. (original) A method for making an integrated circuit, comprising providing alternating areas of electrically insulating and electrically conducting materials within a layer on a semiconductor substrate, wherein the electrically insulating material comprises a poly(organo siloxane) compound deposited via CVD method comprising a repeating Si-O backbone, carbon chain crosslinking groups and -R1-R2 bound to from 5 % to 60 % of the silicon atoms in the Si-O backbone, wherein R2 is an aromatic group having 6 carbon atoms and R1 is a substituent at position 4 of R2 selected from an alkyl chain having from 1 to 4 carbons, an alkenyl group having from 2 to 6 carbons or OH.

64 - 66. (canceled)